

Notice of References Cited	Application/Control No. 10/551,843		Applicant(s)/Patent Under Reexamination OHMI ET AL.	
	Examiner GRANT S. WITHERS		Art Unit 2895	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,876,788 A	03-1999	Bronner et al.	427/81
*	B	US-6,291,866 B1	09-2001	Wallace et al.	257/410
	C	US-			
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	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Visokay, M. R. "Application of HfSiON as a gate dielectric material" App. Phys. Letters Vol. 80 Num 17 04/29/2002 pp. 3183-3185
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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